

BYD Microelectronics Co., Ltd.

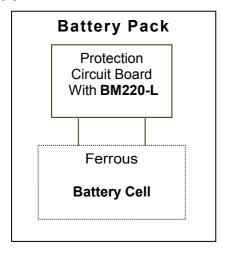
BM220-L-XX Series

Fe Battery Protectors

General Description

The BM220-L series are protection ICs for ferrous rechargeable battery packs. It includes voltage detection unit, voltage reference unit, bias unit, delay unit, and logic circuits. The BM220-L series have cell-balance function and high-accuracy voltage detection for protecting Two-cell ferrous battery packs from overcharge, over-discharge, excess-current and short circuit.

Applications



Features

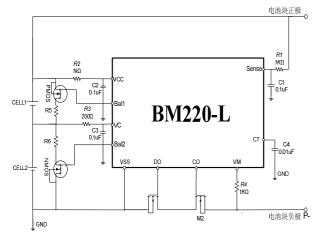
- Overcharge Threshold
 - 3.600~ 4.000V

■ Accuracy Min. ±25mV (25°C)

±50mV (-20°C~70°C)

- Over-discharge Threshold
 - Typ. 2.00V
 - Accuracy Min. ±80mV
- Balance Threshold
 - Typ. 3.62V
 - Accuracy ±0.10V
- Excess Current 1 Protection Threshold
 - Typ. 0.2V @ VC = 2.85V, VCC = 5.7V
 - Accuracy ±0.02V
- Excess Current 2 Protection Threshold
 - Typ. 0.60V @ VC = 2.85V, VCC = 5.7V
 - Accuracy ±0.1V
- Short Circuit Protection Threshold
 - Typ. 1.50V @ VC = 2.85V, VCC = 5.7V
 - Accuracy ±0.5V
- Low power consumption
 - Typ. 10.0uA @ VC = 3.3V, VCC = 6.6V (Standard working current)
 - Typ. 0.9uA @ VC = 1.5V, VCC = 3.0V (Standby current)
- Output Delay of Overcharge
 - Typ. 85ms (connect a 0.01uF cap to CT)
- Output Delay of Over-discharge
 - Typ. 24ms @ VC = 1.9V, VCC = 3.8V

Typical Application Circuits



Notes

 R_1C_1 , R_2C_2 and R_3C_3 are to stabilize the supply voltage of the BM220-L series. R_1C_1 is hence regarded as the time constant for Sense pin. R_2C_2 is hence regarded as the time constant for VCC pin. R_2 and R_4 can also be a part of current-limit circuit for the BM220-L series. Recommended values of these elements are as follows:

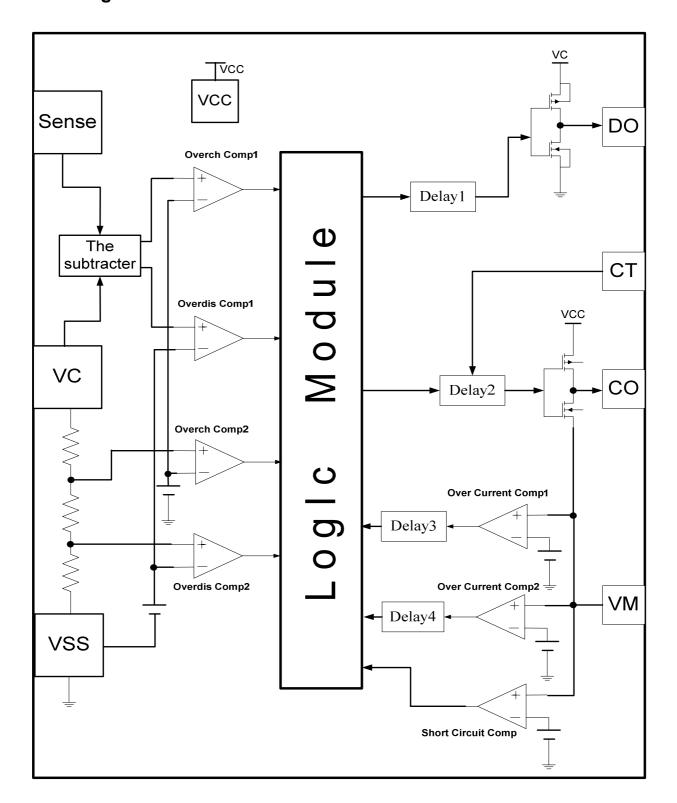
- R₃ < 470Ω. A larger value of R₃ results in high detection voltage, low detection accuracy.
- $R_4 < 2.5k\Omega$. A larger value of R_4 possibly counteracts resetting from over-discharge even with a charger.
- R5, R6 is determined by your balance bypass current. R_2 + R_4 > $2k\Omega$. Smaller values may lead to power consumption over the maximum dissipation rating of the BM220-L series.

Recommended value:

 $R_1=R_2=R_4=1k\Omega$; $R_3=200\Omega$; $C_1=C_2=C_3=0.1uF$



Block Diagram





Selection Guide

Type Number

BM220-L-XX

Symbol	Meaning	Description		
XX	Overcharge/Over-discharge detection threshold and accuracy	Assigned from AA to WW		

Type Number Option

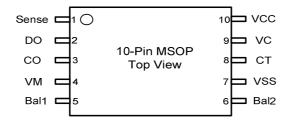
Through choosing the "XX", the Overcharge Detection Threshold Voltage (VCT1,2), the Over-discharge Detection Threshold voltage (VDT1,2), and their accuracy of BM220-L can be decided.

Table 1. VCT1,2 & VDT1,2 & Marking

(@ 25℃)

Type Number VCT1,2 VCT1,2 A		VCT1,2 Accuracy	VDT1,2	VDT1,2 Accuracy	Mark
BM220- L- FM	3.850 V	±25 mV	2.000 V	±80mV	220LM

Package Type



Pin Description

Pin number	Pin name	Description
1	Sense	The overcharge/over-discharge detection pin, for
I		monitoring voltage relative to VC
2	DO	Over-discharge detection pin, CMOS output
3	CO	Overcharge detection pin, CMOS output
4	VM	The excess-current detection pin
5	Bal1	The balance control pin of cell1.
6	Bal2	The balance control pin of cell2.
7	VSS	Ground
8	CT	To connect capacity for Overcharge detection delay
9	VC	The middle pin between two cells (to connect cell 1
9		cathode and cell 2 anode)
10 VCC		Positive power input pin (to connect cell 1 anode)



Function Description

1. Normal Condition:

When both VC and (VCC-VC) are between the Over-discharge Detection Threshold Voltage (VDT) and the Overcharge Detection Threshold Voltage (VCT), and the VM pin voltage between the Charger Detection Threshold Voltage (VCHA) and the Excess Current 1 Detection Threshold Voltage (VIT1), the outputs of DO pin and CO pin are on high level, making the charge and discharge MOSFETs on. Charging and discharging can be carried out freely.

2. Overcharge Condition:

During charging, when VC or (VCC-VC) increases higher than VCT and takes the Overcharge Detection Delay Time (T_{CT}) or longer, the output of CO pin will change from high level to low level, turning off the charging control FET to stop charging.

3. Overcharge Protection Release Condition:

The output of CO pin will change to high level, making charging recovered, when either of the following conditions come into being: (1) both VC and (VCC - VC) become lower than the Overcharge Release Voltage (VCR); (2) a load connects to VCC after a charger is disconnected from the battery pack, and both VC and (VCC - VC) are lower than VCT.

4. Over-discharge Condition:

During discharging, when VC or (VCC - VC) decreases lower than VDT and taking the Over-discharge Detection Delay Time (T_{DT}) or longer, the output of DO pin will change from high level to low level, turning off the discharging control FET to stop discharging.

5. Over-discharge Protection Release Condition:

The output of DO pin will change to high level, making discharging recovered, when either of the following conditions come into being: (1) a charger is connected to the battery pack, and the battery supply voltage becomes higher than VDT, and VM is higher than the Charger Detection Threshold Voltage (VCHA); (2) both the VC and (VCC — VC) become higher than the Over-discharge Release Voltage (VDR) and VM is between VCHA and VIT1.

6. Excess Current 1 Protection:

During discharging, the current varies with load, and VM increases with the rise of the discharging current. Once VM rises higher than the Excess Current 1 Detection Threshold Voltage (VIT1) and stays longer than the Excess Current 1 Detection Delay Time (T₃), DO pin changes from high to low level, turning off the discharging control FET. Once that excess current state is removed, i.e. VM < VIT1, and the circuit recovers to normal state.



7. Excess Current 2 Protection:

During discharging, the current varies with load, and VM increases with the rise of the discharging current. Once VM rises higher than the Excess Current 2 Detection Threshold Voltage (VIT2) and stays longer than the Excess Current 2 Detection Delay Time (T_4) , DO pin changes from high to low level, turning off the discharging control FET. Once that excess current state is removed, and VM < VIT1, and the circuit recovers to normal state.

8. Short Circuit Protection:

This function has the same principle as the excess current protection. But, the delay time T_5 is far shorter than T_3 and T_4 , and the threshold VSHORT is far higher than VIT1 and VIT2. When the circuit is shorted, VM increases rapidly. Once VM \geq VSHORT, DO pin switches to low, turning off the discharging control FET. After the short circuit state is removed, and VM < VIT1, the circuit recovers to the normal state. The short circuit peak current is related to VSHORT and the ON resistance of the two FETs in series.

9. Cell-balance Function: The cell-balance function is used to balance the two cells' voltage in the pack. When the (VCC-VC) is between the Cell-balance1 Threshold (VBAL1) and the Overcharge Detection Voltage(VCT), and VC is below the Cell-balance 2 Threshold (Vbal2) for the Cell-balance 1 Detection Delay Time(T_{BAL1}) or longer, the Bal1 pin controls the

P-MOSFET to switch on the bypass balance circuit. When the (VCC-VC) is higher than the Overcharge Detection Threshold Voltage (VCT), or the VC is higher than the Cell-balance 2 Threshold (Vbal2), the bypass balance circuit is switched off by the P-MOSFET.

As the same, when the VC is between the Cell-balance 2 Threshold (VBAL2) and the Overcharge Detection Threshold Voltage (VCT), and (VCC-VC) is below the Cell-balance 1 Threshold (VBAL1) for the Cell-balance 2 Detection Delay Time(TBAL2) or longer, the Bal2 pin controls the N-MOSFET to switch on the other bypass balance circuit. When the VC is higher than the Overcharge Detection Threshold Voltage (VCT) or the (VCC-VC) is higher than the Cell-balance Threshold 1(VBAL1), the bypass balance circuit is switched off by the N-MOSFET.

10. Abnormal Charge Current Condition:

If the VM pin voltage falls below the Abnormal Charge Current Detection Threshold Voltage (VAB) during charging under normal condition and takes the Abnormal Charge Current Detection Delay Time (TAB) or longer, the charging control FET is turned off and charging stops. This action is called the Abnormal Charge Current Detection. Abnormal charge current detection works when the DO pin voltage is "H" and the VM pin voltage falls below the Abnormal Charge Current Detection Threshold Voltage (VAB). To an over-discharged battery, only when charging makes the battery voltage higher than the Over-discharge Detection Threshold (VDT), the



Abnormal Charge Current Detection can act. Abnormal charge current state is released, once the voltage difference between VM pin and VSS pin becomes less than the Abnormal Charge Current Detection Threshold Voltage (VAB) value.

11. Charger Detect Condition:

A two-cell battery in over-discharge condition can be released, when it is connected to a charger, the VM pin voltage is lower than the Abnormal Charge Current

Detection Threshold Voltage (VAB), and each cell voltage becomes higher than the Over-discharge Detection Threshold Voltage (VDT). This action is called Charger Detection. But, if the VM pin voltage is between the Abnormal Charge Current Detection Threshold Voltage (VAB) and the Excess Current 1 Detection Threshold Voltage (VIT1), the over-discharge state is not released unless the two cell voltages both become higher than the Over-discharge Release Voltage (VDR).

Electrical Characteristic 1x

Item	Symbol	Condition	Min.	Тур.	Max.	Unit	Circuit
Operation Voltage							
Operation Voltage between	VDSOP	20~85℃	2		16	V	
VCC and VSS	VDOOP	20~65 C	2		10	V	
Detection Voltage							
Over Charge Detection Voltage 1,2	VCT1,22×	25 ℃	VCT1,2-0.025	VCT1,2	VCT1,2+0.025	٧	1
Overcharge Release Voltage 1,2	VCR1,23×	25℃	VCT1,2-0.4	VCT1,2-0.3	VCT1,2-0.2	V	1
Over-discharge Detection Voltage 1,2	VDT1,22×	25℃	VDT1,2-0.08	VDT1,2	VDT1,2+0.08	V	2
Over-discharge Release Voltage 1,2	VDR1,23×	25℃	VDT1,2+0.6	VDT1,2+0.7	VDT1,2+0.8	V	2
Excess current 1 Detection Voltage	VIT1	VC = 2.85V	0.18	0.2	0.22	V	3
Excess current 2 Detection Voltage	VIT2	VC = 2.85V	0.5	0.6	0.7	V	3
Short Circuit Detection Voltage	VSHORT	VC = 2.85V	1	1.5	2	V	3
Cell-balance 1 threshold	VBAL1	25℃	3.52	3.62	3.72	V	7
Cell-balance 2 threshold	VBAL2	25 ℃	3.52	3.62	3.72	V	7
Abnormal Charge Detection Voltage	VAB	25 ℃	-0.17	-0.15	-0.13	V	6
Charger Detection Voltage	VCHA	25℃	-0.17	-0.15	-0.13	٧	6
Delay Time (C₄=0.01u F)			•		•		
Over Charge Detection Delay Time	Тст	VC = 3.90V	42	85	170	ms	5
Over Discharge Detection Delay Time	T _{DT}	VC = 1.90V	12	24	48	ms	2
Over Current 1 Detection Delay Time	T ₃	VC = 2.85V	6	12	24	ms	3
Over Current 2 Detection Delay Time	T ₄	VC = 2.85V	1	2	3	ms	3
Short Circuit Detection Delay Time	T ₅	VC = 2.85V			10	us	3
Abnormal Charge Detection Delay Time	Тав	VC = 2.85V	42	85	170	ms	3
Cell-balance 1 Detection Delay Time	T _{BAL1}	VC = 2.85V	1	2	3	ms	7
Cell-balance 2 Detection Delay Time	T _{BAL2}	VC = 2.85V	1	2	3	ms	7
Output Voltage			•		•		
OO "I !" \/-I+	VCO(II)	VCC = 6.8V	0.50	0.0		\/	0
CO "H" Voltage	VCO(H)	VC = 3.4V	6.58	6.6		V	8
CO "L" Voltage	VCO(L)	VCC = 7.4V		0.4	0.40	V	8
CO L Voltage	VCO(L)	VC = 3.4V		0.1	0.12		
DO "H" Voltage	VDO(H)	VCC = 6.8V	3.30	3.32		٧	8
DO 11 Voltage	VDO(H)	VC = 3.4V	3.30	3.32		V	0
DO "L" Voltage	VDO(L)	VCC = 4.9V		0.05	0.07	V	8
-		VC = 3.4V		0.00	0.01	•	
Current consumption		ı	ı	· · · · · · · · · · · · · · · · · · ·	-		
Current Consumption during Normal state	IOPE	V1 = V2 = 3.3	5	10	15	uA	4
Current Consumption during Power Down	I _{PDN}	V1 = V2 = 1.5	0.5	0.9	1.5	uA	4

^{1*} The Electrical parameters for this temperature range is guaranteed by design, not tested in production.

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^{2*} See "Selection Guide" section.

^{3*} VCT1,2 and VDT1,2 are the Overcharge and Over-discharge threshold voltage of actual testing.



Absolute Maximum Ratings

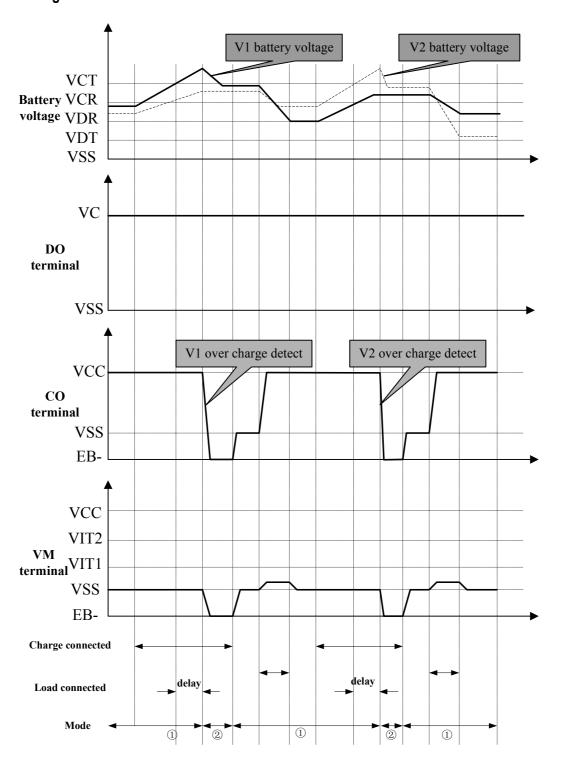
Item	Symbol	Pin	Rated Value	Unit
VCC-VSS input voltage	V _{DS}	VCC	VSS-0.3~VSS+18	V
Sense pin input voltage	V _{Sense}	Sense	VSS-0.3~VCC+0.3	V
Delay pin input voltage	V _{CT}	CT	VSS-0.3~VCC+0.3	V
VM pin input voltage	Vvм	VM	VCC-28~VCC+0.3	V
DO pin output voltage	V_{DO}	DO	VSS-0.3~VC+0.3	V
CO pin output voltage	V _{CO}	CO	VM-0.3~VCC+0.3	V
Power Dissipation	P _D		300	mW
Operation Temperature	T _{opr}		-20~+85	$^{\circ}$
Storage Temperature	T _{stg}		-40~+125	$^{\circ}$

Attention: Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.



Operation Timing Charts:

Overcharge:



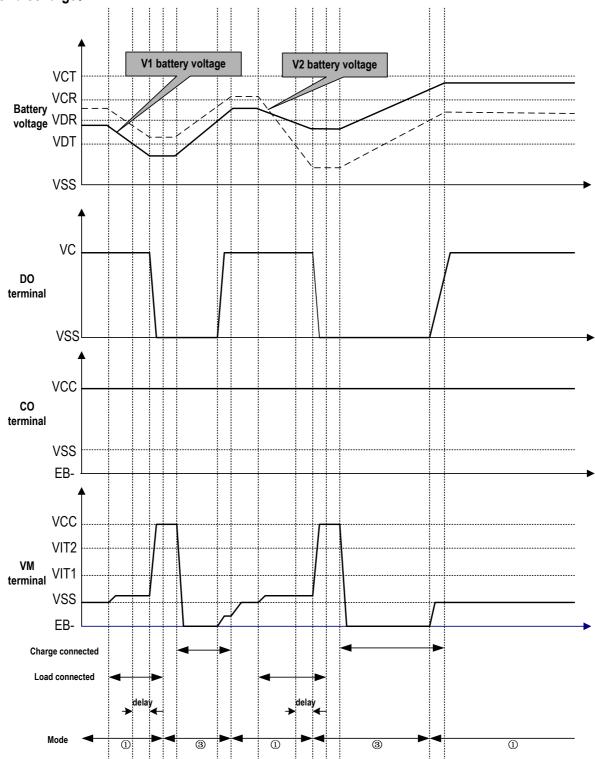
Note: ① Normal mode ② Overcharge mode ③ Over-discharge mode

④ Excess current 1 mode ⑤ Excess current 2 mode

6 Short circuit mode 7 Bypass current work mode



Over-discharge:



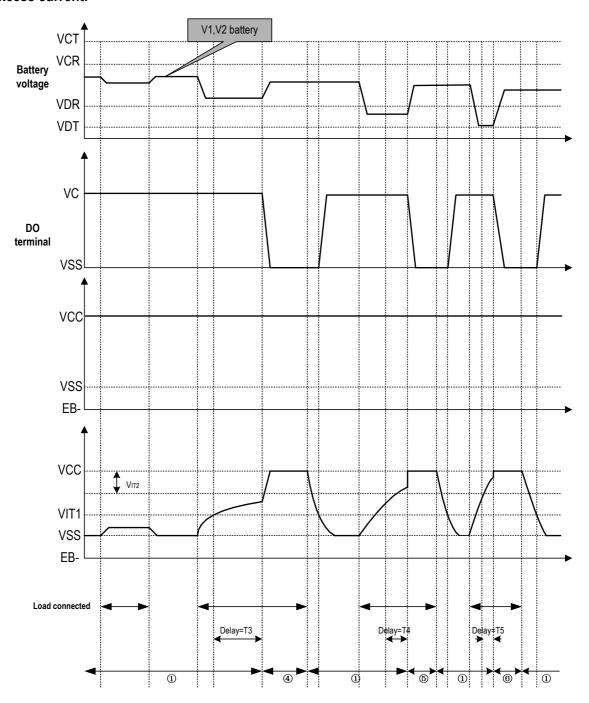
Note: ① Normal mode ② Overcharge mode ③ Over-discharge mode

4 Excess current 1 mode 5 Excess current 2 mode

⑥ Short circuit mode ⑦ Bypass current work mode



Excess current:



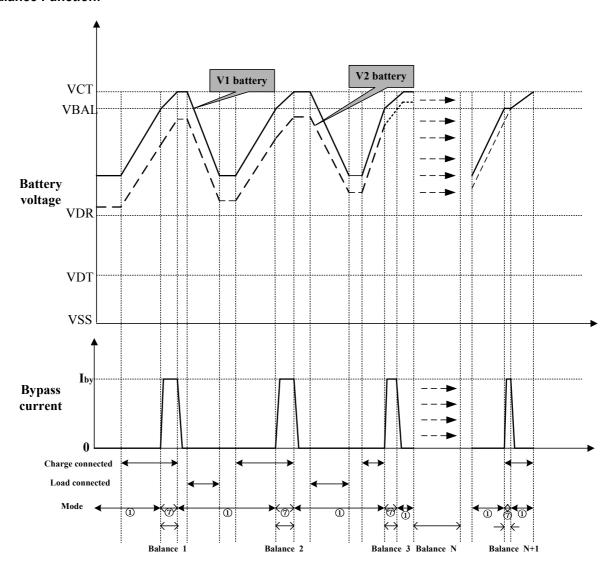
Note: ① Normal mode ② Overcharge mode ③ Over-discharge mode

4 Excess current 1 mode 5 Excess current 2 mode

⑥ Short circuit mode ⑦ Bypass current work mode



Cell-balance Function:



Note: ① Normal mode ② Overcharge mode ③ Over-discharge mode

4 Excess current 1 mode 5 Excess current 2 mode

⑥ Short circuit mode ⑦ Bypass current work mode



Test Circuits

(1) Overcharge detection threshold voltage and overcharge release voltage

Test circuit 1

Set V2=3.3V,the Overcharge Detection Threshold Voltage (VCT1) is the voltage between VCC and VC to which when V1 increases and keeps the condition for the Overcharge Detection Delay Time (T_{CT}), VCO changes from "H" to "L". The overcharge release voltage (VCR1) is the voltage between VCC and VC to which when V1 decreases, VCO changes from "L" to "H".

Set V1=3.3V, the Overcharge Detection Threshold Voltage (VCT2) is the voltage between VC and VSS to which when V2 increases and keeps the condition for the Overcharge Detection Delay Time (T_{CT}), VCO changes from "H" to "L". The Overcharge Release Voltage (VCR2) is the voltage between VC and VSS to which when V1 decreases, VCO changes from "L" to "H".

(2) Over-discharge detection threshold voltage and over-discharge release voltage Test circuit 2

Set V2=3.3V, the Over-discharge Detection Threshold Voltage (VDT1) is the voltage between VCC and VC to which when V1 decreases and keep the condition for the Over-discharge Detection Delay Time (T_{DT}), VDO changes from "H" to "L". The Over-discharge Release Voltage (VDR1) is the voltage between VC and VSS to which when V1 increases, VDO changes from "L" to "H".

Set V1=3.3V, the Over-discharge Detection Threshold Voltage (VDT2) is the voltage between VC and VSS to which when V2 decreases and keep the condition for the Over-discharge Detection Delay Time (T_{DT}), VDO changes from "H" to "L". The Over-discharge Release Voltage (VDR2) is the voltage between VC and VSS to which when V1 increases, VDO changes from "L" to "H".

(3) Excess current detection threshold voltage and short circuit detection threshold voltage

Test circuit 3

Set V1=2.85V V2=2.85V,the Excess Current 1 Detection Threshold Voltage (VIT1) is the voltage V3 between VM and VSS to which when VM increases within 10 us and keep the

condition for the Excess Current 1 Detection Delay Time (T₃), VDO changes from "H" to "L".

The Excess Current 2 Detection Threshold Voltage (VIT2) is the voltage V3 between VM and VSS to which when VM increases within 10 us and keep the condition for the Excess Current 2 Detection Delay Time (T₄), VDO changes from "H" to "L".

The Short Circuit Detection Threshold Voltage (VSHORT) is the voltage V3 between VM and VSS to which when VM increases within 10us and keep the condition for the Short Circuit Detection Delay Time (T5), VDO changes from "H" to "L".

(4) Normal operation current consumption and power down current consumption

Test circuit 4

Set V1=3.3V V2=3.3V, the current A1 flowing through VCC and Sense pin and the current A2 flowing through VC pin are the normal operation consumption current (I_{OPE}). Set V1=1.5V V2=1.5V, the current A1 flowing through VCC and Sense pin and the current A2 flowing through VC pin

(5) Overcharge detection delay time and over-discharge detection delay time

are the power down current consumption (IPDN).

Test circuit 5

If V1 or V2 increases to be VCT1 or over VCT1 and keeps the condition for some time, VCO will change from "H" to "L". The time is called Overcharge Detection Delay Time (T_{CT}). It is used to judge whether overcharge happens indeed.

Test circuit 2

If V1 or V2 decreases to be VDT1 or below VDT1 and keeps the condition for some time, VDO will change from "H" to "L". The time is called Over-discharge Detection Delay Time (T_{DT}). It is used to judge whether over-discharge happens indeed.

(6) Excess current detection delay time and short circuit detection delay time

Test circuit 3

If V3 increases to be VIT1 or over VIT1 and keeps the condition for some time, VDO will change from "H" to "L". The time is called Excess Current 1 Detection Delay Time (T₃). It is used to judge whether excess current 1 happens



indeed.

If V3 increases to be VIT2 or over VIT2 and keeps the condition for some time, VDO will change from "H" to "L". The time is called Excess Current 2 Detection Delay Time (T₄). It is used to judge whether excess current 2 happens indeed.

If V3 increases to be VSHORT or over VSHORT and keeps the condition for some time, VDO will change from "H" to "L". The time is called Short Circuit Delay Time (T₅). It is used to judge whether short circuit happens indeed.

(7) Charger detection threshold voltage and abnormal charge current detection threshold voltage

Test circuit 6

In the over-discharge condition, increase V2 gradually until it is between VDT2 and VDR2. The voltage between VM and VSS to which when V3 increases, VDO changes from "L" to "H", is the Charger Detection Threshold Voltage (VCHA).

In the normal charging condition, the voltage between VM and VSS to which when V3 increases, VCO changes from "H" to "L" is the Abnormal Charge Current Detection Threshold Voltage (VAB). It has the same value as the Charger Detection Threshold Voltage (VCHA).

(8) Cell-balance threshold

Test Circuit 7

Set V2=3.3V,the Cell-balance1 threshold (VBAL1) is the voltage between VCC and VC to which when V1 increases and keeps the condition for Cell-balance 1 Detection Delay Time (T_{BAL1}), V_{Bal1} changes from "H" to "L".

Set V1=3.3V, the overcharge detection voltage (VCT2) is the voltage VC which when V2 increases and keeps the condition for Cell-balance Detection 2 Delay Time (T_{BAL2}), VBal2 changes from "L" to "H".

(9) Cell-balance Detection Delay Time

Test Circuit 7

Set V2=3.3V, If V1 increases to be VBAL1 or over VBAL1 but lower than VCT1 and keeps the condition for some time, VBall will change from "H" to "L". The time is called cell-balance 1 detection delay time. It is used to judge whether a bypass balance current is need indeed.

Set V1=3.3V, If V2 increases to be VBAL2 or over VBAL2

but lower than VCT2 and keeps the condition for some time, VBal2 will change from "L" to "H". The time is called cell-balance 2 detection delay time. It is used to judge whether a bypass balance current is need indeed.

(10) CO and DO output voltage

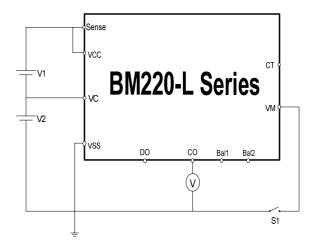
Test Circuit 8

Set S1=ON, V1=V2=3.4V under normal condition. Increase V4 from 0V gradually, the V4 voltage when A2 = 50 uA is the CO 'H' voltage (VCOH).

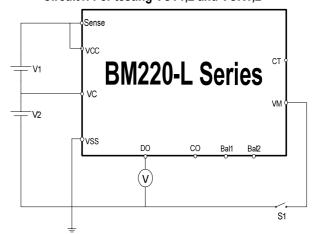
Set S1=ON, V1=4V, V2=3.4V. Decrease V4 from 0V gradually, the V4 voltage when A2 =50 uA is the CO 'L' voltage (VCOL).

Set S1=ON, V1=V2=3.4V under normal condition. Increase V3 from 0V gradually, the V4 voltage when A1 = 50 uA is the DO 'H' voltage (VDOH).

Set S1=ON, V1=1.5V, V2=3.4V. Decrease V3 from 0V gradually, the V4 voltage when A1 =50 uA is the CO 'L' voltage (VCOL).

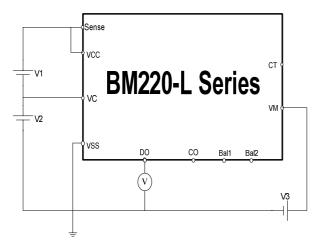


Circuit1: For testing VCT1,2 and VCR1,2

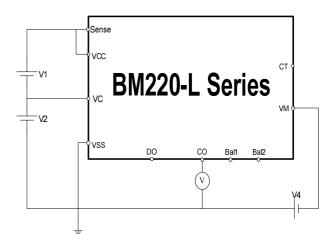


Circuit2: For testing VDT1,2 and VDR1,2

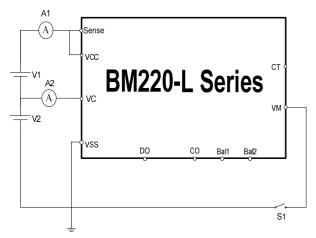




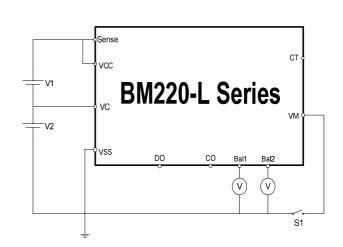
Circuit3: For testing VIT1,2 and V_{SHORT}



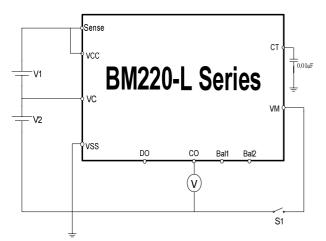
Circuit6: For testing VAB and VCHA



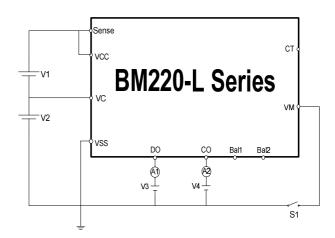
Circuit4: For testing lope and IPDN



Circuit7: For testing VBAL1,2 and TBAL1,2



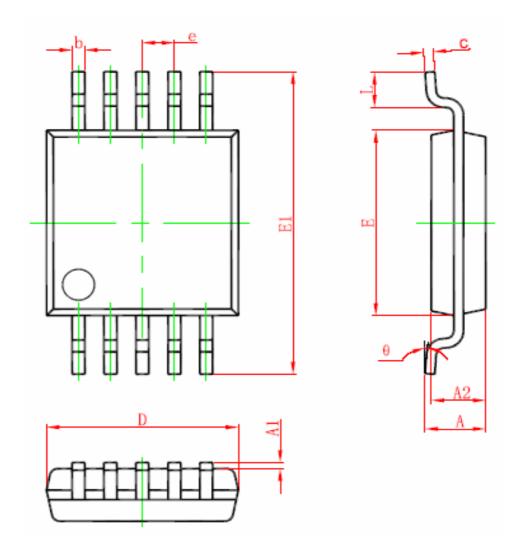
Circuit5: For testing TcT



Circuit8: For testing CO and DO output voltage



Package Outline



 Dimensions
 UNIT (mm)

 A
 A1
 A2
 b
 c
 D
 e
 E
 E1
 L

	A	A1	A2	b	С	D	е	E	E1	L	θ
Min.	0.820	0.020	0.750	0.180	0.090	2.900	0.50	2.900	4.750	0.400	0°
Max.	1. 100	0.150	0.950	0. 280	0.230	3. 100	BSC	3. 100	5.050	0.800	6°

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